



SB4045LCT

DUAL LOW VF SCHOTTKY RECTIFIER

VOLTAGE 45 Volts **CURRENT** 40 Amperes

FEATURES

- Low forward voltage drop, low power losses
- High efficiency operation
- In compliance with EU RoHS 2002/95/EC directives

MECHANICAL DATA

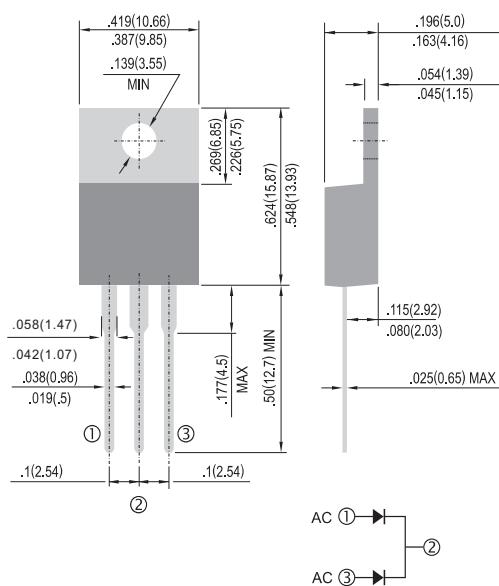
Case : TO-220AB, Plastic

Terminals : Solderable per MIL-STD-750, Method 2026

Weight: 0.0655 ounces, 1.859 grams

TO-220AB

Unit: inch (mm)



MAXIMUM RATINGS(T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	VALUE	UNIT
Maximum repetitive peak reverse voltage	V _{RRM}	45	V
Maximum average forward rectified current (Fig.1)	I _{F(AV)} per device per diode	40 20	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load per diode	I _{FSM} per diode	250	A
Typical Thermal Resistance	R _{θJC}	2.5	°C/W
Operating junction	T _J	-55 to + 125	°C
Storage temperature range	T _{STG}	-55 to + 150	°C

ELECTRICAL CHARACTERISTICS(T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Breakdown voltage	V _{BR}	I _R =1mA	49	-	-	V
Instantaneous forward voltage per diode ⁽¹⁾	V _F	I _F =10A T _J =25°C	-	0.44 0.51	0.48 0.53	V
		I _F =10A T _J =125°C	-	0.36 0.50	- 0.55	V
Reverse current per diode ⁽²⁾	I _R	V _R =45V T _J =25°C T _J =100°C	-	-	500 100	μA mA

Note.1.Pulse test : 300μs pulse width, 1% duty cycle

2.Pulse test : pulse width ≤ 40ms

PAN JI T RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE



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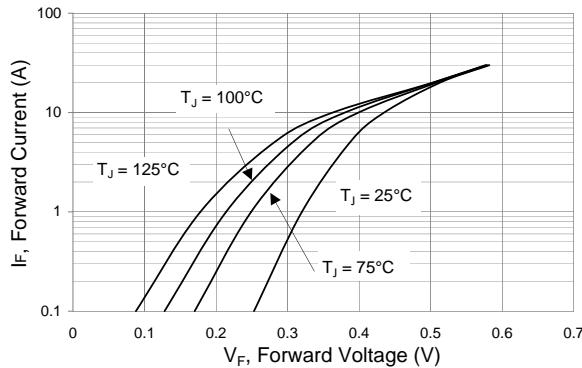


Fig.1 Typical Forward Characteristics Per Diode

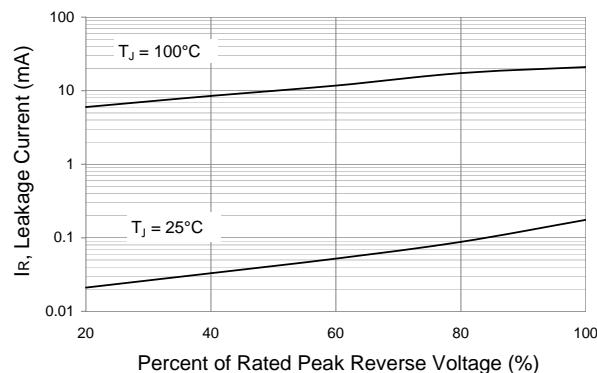


Fig.2 Typical Reverse Characteristics Per Diode

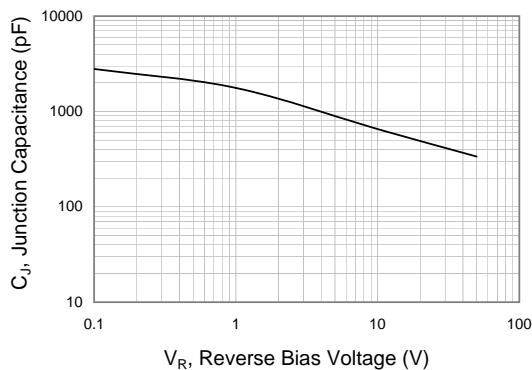


Fig.3 Typical Junction Capacitance Per Diode

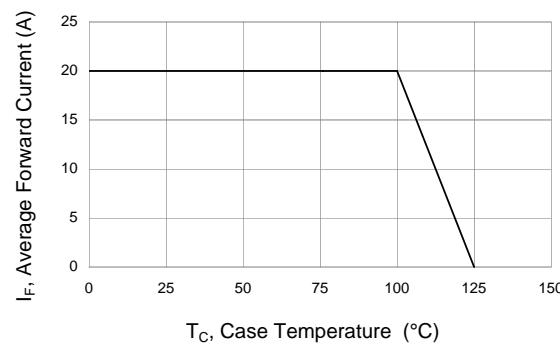


Fig.4 Forward Current Derating Curve Per Diode